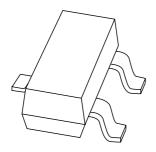
## **DISCRETE SEMICONDUCTORS**

## DATA SHEET



# **BSR15**; **BSR16**PNP switching transistors

Product data sheet Supersedes data of 1999 Apr 15 2004 Jan 13



## **PNP** switching transistors

**BSR15**; **BSR16** 

#### **FEATURES**

- High current (max. 600 mA)
- Low voltage (max. 60 V).

#### **APPLICATIONS**

· Medium power switching.

#### **DESCRIPTION**

PNP switching transistor in a SOT23 plastic package. NPN complements: BSR13 and BSR14.

#### **MARKING**

TYPE NUMBER	MARKING CODE <sup>(1)</sup>
BSR15	T7*
BSR16	T8*

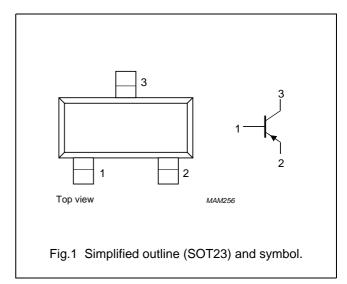
#### Note

1. \* = p: Made in Hong Kong.

\* = t : Made in Malaysia. \* = W : Made in China.

#### **PINNING**

PIN	DESCRIPTION
1	base
2	emitter
3	collector



#### **ORDERING INFORMATION**

TYPE	PACKAGE		
NUMBER	NAME	DESCRIPTION	VERSION
BSR15	_	plastic surface mounted package; 3 leads	SOT23
BSR16			

## PNP switching transistors

BSR15; BSR16

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	_	-60	V
$V_{CEO}$	collector-emitter voltage	open base			
	BSR15		_	-40	V
	BSR16		_	-60	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	-5	V
Ic	collector current (DC)		_	-600	mA
I <sub>CM</sub>	peak collector current		_	-800	mA
I <sub>BM</sub>	peak base current		_	-200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	_	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	note 1	500	K/W

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

## PNP switching transistors

BSR15; BSR16

#### **CHARACTERISTICS**

 $T_j = 25$  °C unless otherwise specified.

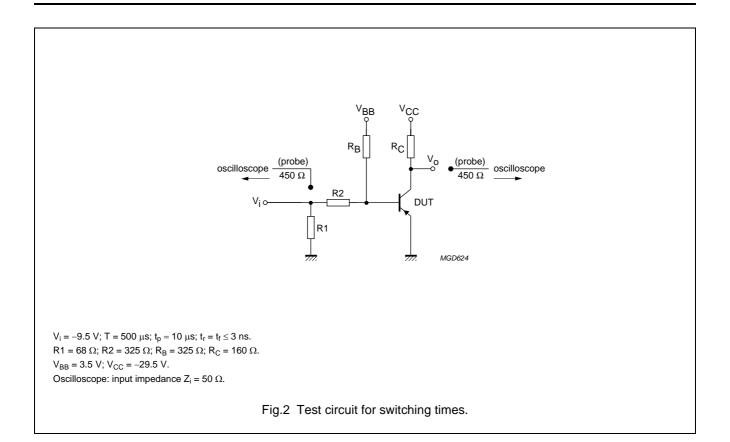
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>CBO</sub>	collector cut-off current				
	BSR15	$I_E = 0$ ; $V_{CB} = -50 \text{ V}$	_	-20	nA
		$I_E = 0$ ; $V_{CB} = -50 \text{ V}$ ; $T_j = 150 ^{\circ}\text{C}$	_	-20	μΑ
	collector cut-off current				
	BSR16	$I_E = 0$ ; $V_{CB} = -50 \text{ V}$	_	-10	nA
		$I_E = 0$ ; $V_{CB} = -50 \text{ V}$ ; $T_j = 150 ^{\circ}\text{C}$	_	-10	μΑ
I <sub>EBO</sub>	emitter cut-off current	$I_C = 0; V_{EB} = -5 \text{ V}$	_	-50	nA
h <sub>FE</sub>	DC current gain	$I_C = -0.1 \text{ mA}; V_{CE} = -10 \text{ V}$			
	BSR15		35	_	
	BSR16		75	_	
	DC current gain	$I_C = -1 \text{ mA}; V_{CE} = -10 \text{ V}$			
	BSR15		50	_	
	BSR16		100	_	
	DC current gain	$I_C = -10 \text{ mA}; V_{CE} = -10 \text{ V}$			
	BSR15		75	_	
	BSR16		100	_	
	DC current gain	$I_C = -150 \text{ mA}$ ; $V_{CE} = -10 \text{ V}$ ; note 1	100	300	
	DC current gain	$I_C = -500 \text{ mA}$ ; $V_{CE} = -10 \text{ V}$ ; note 1			
	BSR15		30	_	
	BSR16		50	_	
V <sub>CEsat</sub>	collector-emitter saturation	$I_C = -150 \text{ mA}; I_B = -15 \text{ mA}$	_	-400	mV
	voltage	$I_C = -500 \text{ mA}$ ; $I_B = -50 \text{ mA}$	_	-1.6	V
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C = -150 \text{ mA}; I_B = -15 \text{ mA}$	_	-1.3	V
		$I_C = -500 \text{ mA}; I_B = -50 \text{ mA}$	_	-2.6	V
C <sub>c</sub>	collector capacitance	$I_E = i_e = 0$ ; $V_{CB} = -10 \text{ V}$ ; $f = 1 \text{ MHz}$	_	8	pF
Ce	emitter capacitance	$I_C = I_c = 0$ ; $V_{EB} = -2$ V; $f = 1$ MHz	_	30	pF
f <sub>T</sub>	transition frequency	$I_C = -50 \text{ mA}$ ; $V_{CE} = -20 \text{ V}$ ; $f = 100 \text{ MHz}$	200	_	MHz
Switching t	imes (between 10% and 90% leve	els); (see Fig.2)	•	•	
t <sub>on</sub>	turn-on time	I <sub>Con</sub> = -150 mA; I <sub>Bon</sub> = -15 mA;	_	40	ns
t <sub>d</sub>	delay time	I <sub>Boff</sub> = 15 mA	_	12	ns
t <sub>r</sub>	rise time		_	30	ns
t <sub>off</sub>	turn-off time		_	365	ns
t <sub>s</sub>	storage time		_	300	ns
t <sub>f</sub>	fall time		_	65	ns

#### Note

1. Pulse test:  $t_p \leq 300~\mu s;~\delta \leq 0.02.$ 

## PNP switching transistors

## BSR15; BSR16



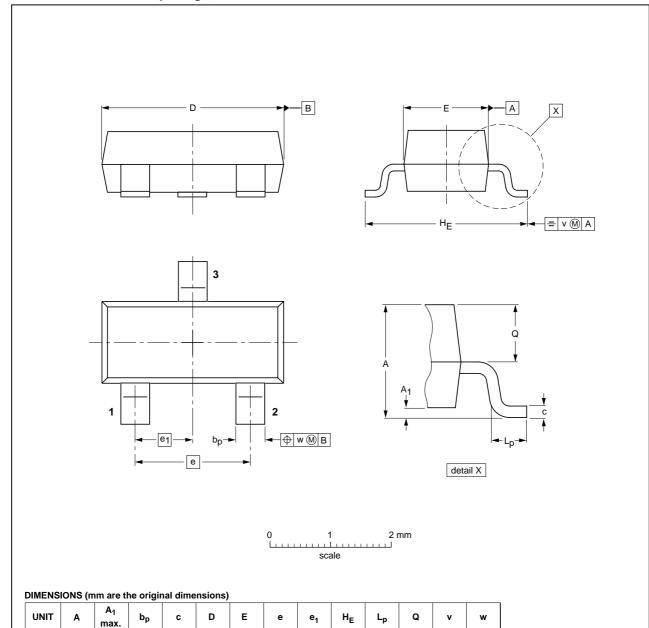
## PNP switching transistors

BSR15; BSR16

#### **PACKAGE OUTLINE**

#### Plastic surface-mounted package; 3 leads

SOT23



OUTLINE	REFERENCES			EUROPEAN	ICCUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT23		TO-236AB				<del>-04-11-04-</del> 06-03-16

1.9

0.45

0.55

0.1

2004 Jan 13 6

max

0.9

0.48

0.38

### PNP switching transistors

**BSR15**; **BSR16** 

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### **Notes**

- 1. Please consult the most recently issued document before initiating or completing a design.
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#### **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

#### **Contact information**

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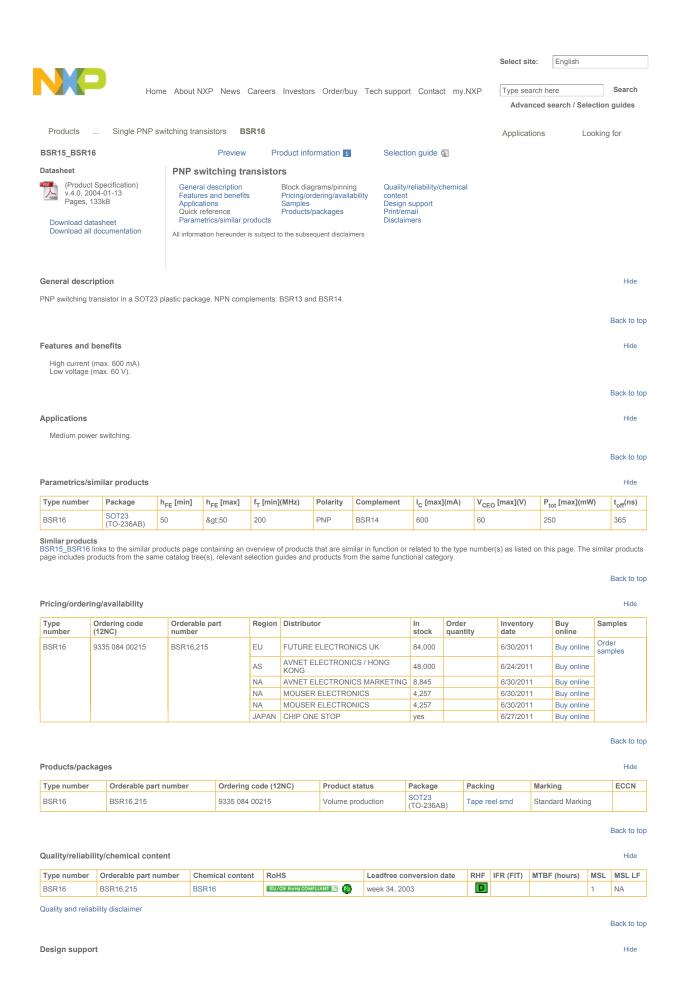
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Other type Letter Symbols - Transistors; General (v.1.0, 1999-05-07)	
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